

## THE SPECIFICATION OF AlGaAs IR LED CHIP “YL-IR4J-S75”

### 1. DESCRIPTION

This is a AlGaAs infrared LED chip. It is N-side up. The peak wavelength is 870 nm (Typ.).

### 2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25deg. C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (V <sub>F</sub> ) IF=20mA		1.39		V
Reverse Voltage (V <sub>R</sub> ) IR=10uA	5			V
Radiated Power <sup>1)</sup> (P <sub>o</sub> ) IF=20mA	4.8			mW
Peak Wavelength (λ <sub>p</sub> ) IF=20mA	860	870	900	nm
Spectral Radiation Bandwidth (Δλ) IF=20mA		45		nm
Rise Time (Tr) IFp=500mA Tw=125ns,Duty=25%		20	35	ns
Fall Time (Tf) IFp=500mA Tw=125ns,Duty=25%		20	35	ns
PeakForward Voltage (V <sub>fm</sub> )IFp=400mA Tw=100 μ s,Duty=10%		2.40		V

1) LED chip is mounted on TO-18 gold header without resin coated.

### 3. ABSOLUTE MAXIMUM RATINGS

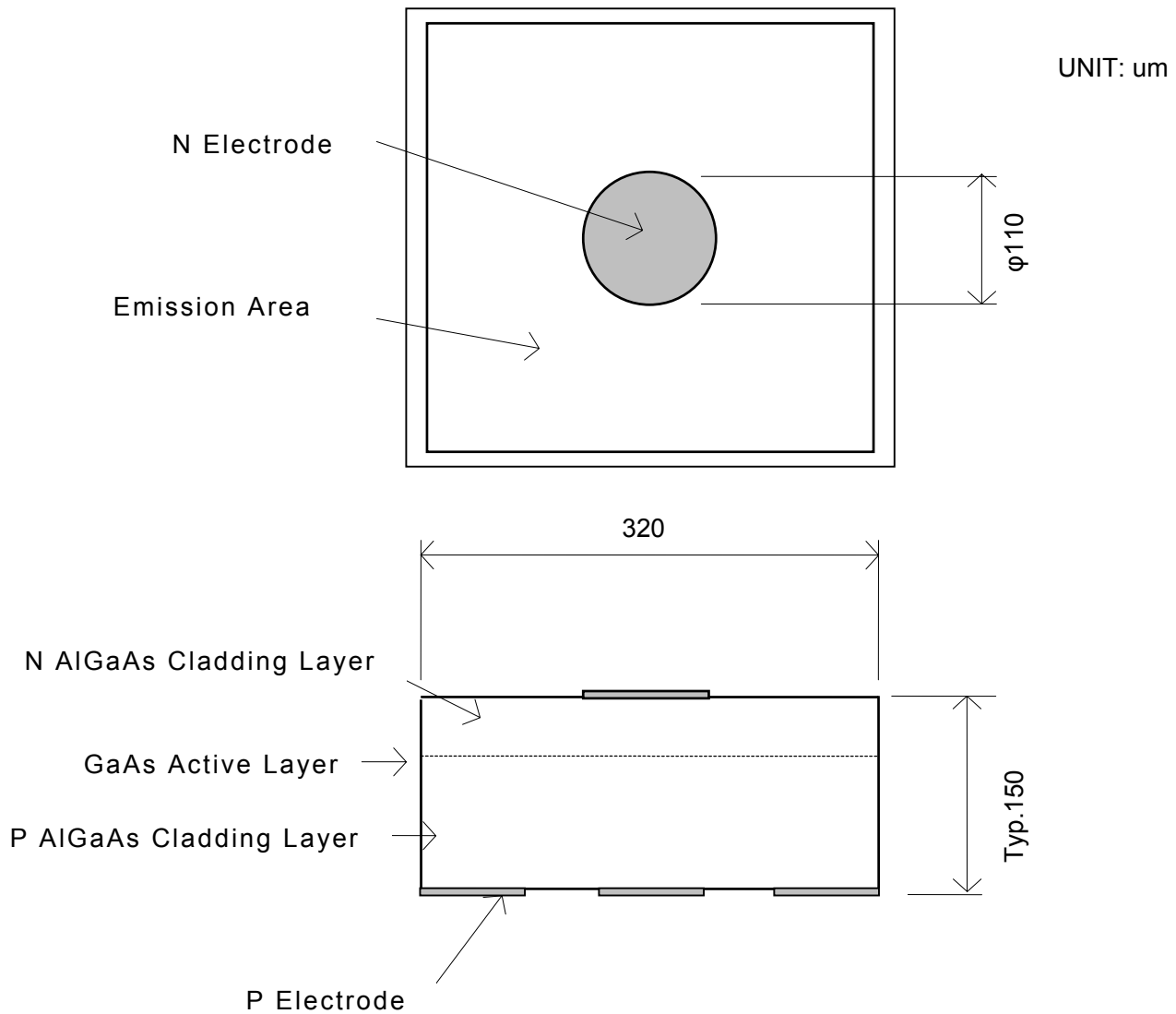
Continuous Maximum Forward Current	: 100 mA(DC)
Reverse Voltage	: 5 V(IR=10uA)
Storage Temperature	
while on mylar membrane	: 0 to 40 deg. C
after removal from mylar membrane	: -40 to 100 deg. C

### 4. PHYSICAL CHARACTERISTICS AND STRUCTURE

- 1)Material : AlGaAs
- 2)Structure : Double Hetero Structure
- 3)Junction Size : 0.320mmX0.320mm
- 4)Thickness : 0.150mm
- 5)Bond Pad Size : 0.110mm diameter
- 6)Anode Metallization : Gold Alloy
- 7)Cathode Metallization: Gold Alloy

## Physical Dimensions

Model YL-IR4J-S75



Remark: This specification is for reference purpose only, and subject to change without prior notice.  
Approved specification shall be obtained for the regular purchase.